## 1-Kb, 2-Kb and 4-Kb SPI Serial CMOS EEPROM

#### Description

The CAV25010/20/40 are 1-Kb/2-Kb/4-Kb Serial CMOS EEPROM devices internally organized as 128x8/256x8/512x8 bits. They feature a 16-byte page write buffer and support the Serial Peripheral Interface (SPI) protocol. The device is enabled through a Chip Select ( $\overline{CS}$ ) input. In addition, the required bus signals are a clock input (SCK), data input (SI) and data output (SO) lines. The HOLD input may be used to pause any serial communication with the CAV25010/20/40 device. These devices feature software and hardware write protection, including partial as well as full array protection.

#### Features

- Automotive Temperature Grade 1 (-40°C to +125°C)
- 10 MHz SPI Compatible
- 2.5 V to 5.5 V Supply Voltage Range
- SPI Modes (0,0) & (1,1)
- 16-byte Page Write Buffer
- Self-timed Write Cycle
- Hardware and Software Protection
- Block Write Protection
  - Protect 1/4, 1/2 or Entire EEPROM Array
- Low Power CMOS Technology
- 1,000,000 Program/Erase Cycles
- 100 Year Data Retention
- Industrial and Extended Temperature Range
- SOIC and TSSOP 8-Lead Packages
- These Devices are Pb–Free, Halogen Free/BFR Free, and RoHS Compliant

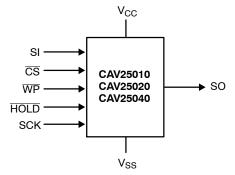


Figure 1. Functional Symbol

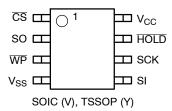


#### **ON Semiconductor®**

http://onsemi.com



#### **PIN CONFIGURATION**



For the location of Pin 1, please consult the corresponding package drawing.

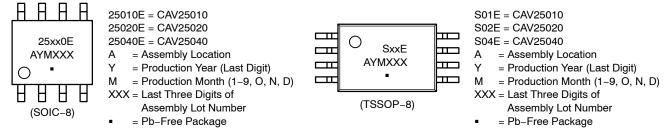
#### **PIN FUNCTION**

Pin Name	Function	
CS	Chip Select	
SO	Serial Data Output	
WP	Write Protect	
V <sub>SS</sub>	Ground	
SI	Serial Data Input	
SCK	Serial Clock	
HOLD	Hold Transmission Input	
V <sub>CC</sub>	Power Supply	

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

#### MARKING DIAGRAMS



#### Table 1. ABSOLUTE MAXIMUM RATINGS

Parameters	Ratings	Units
Operating Temperature	–45 to +130	°C
Storage Temperature	−65 to +150	°C
Voltage on any Pin with Respect to Ground (Note 1)	–0.5 to V <sub>CC</sub> + 0.5	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### Table 2. RELIABILITY CHARACTERISTICS (Note 2)

Symbol	Parameter	Min	Units
N <sub>END</sub> (Note 3)	Endurance	1,000,000	Program / Erase Cycles
T <sub>DR</sub>	Data Retention	100	Years

#### Table 3. D.C. OPERATING CHARACTERISTICS (V<sub>CC</sub> = 2.5 V to 5.5 V, T<sub>A</sub> = -40°C to +125°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Min	Max	Units
I <sub>CCR</sub>	Supply Current (Read Mode)	Read, $V_{CC}$ = 5.5 V, 10 MHz, SO open		2	mA
ICCW	Supply Current (Write Mode)	Write, $V_{CC}$ = 5.5 V, 10 MHz, SO open		2	mA
I <sub>SB1</sub>	Standby Current	$V_{IN} = GND \text{ or } V_{CC}, \overline{CS} = V_{CC},$ $\overline{WP} = V_{CC}, V_{CC} = 5.5 \text{ V}$		2	μΑ
I <sub>SB2</sub>	Standby Current	$V_{IN} = GND \text{ or } V_{CC}, \overline{CS} = V_{CC},$ $\overline{WP} = GND, V_{CC} = 5.5 \text{ V}$		5	μΑ
١L	Input Leakage Current	$V_{IN} = GND \text{ or } V_{CC}$	-2	2	μΑ
I <sub>LO</sub>	Output Leakage Current		-1	2	μΑ
V <sub>IL</sub>	Input Low Voltage		-0.5	0.3 V <sub>CC</sub>	V
VIH	Input High Voltage		0.7 V <sub>CC</sub>	V <sub>CC</sub> + 0.5	V
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 3.0 mA		0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -1.6 mA	V <sub>CC</sub> – 0.8 V		V

#### Table 4. PIN CAPACITANCE (Note 2) (T<sub>A</sub> = 25°C, f = 1.0 MHz, V<sub>CC</sub> = +5.0 V)

Symbol	Test	Conditions	Min	Тур	Max	Units
C <sub>OUT</sub>	Output Capacitance (SO)	V <sub>OUT</sub> = 0 V			8	pF
C <sub>IN</sub>	Input Capacitance (CS, SCK, SI, WP, HOLD)	V <sub>IN</sub> = 0 V			8	pF

1. The DC input voltage on any pin should not be lower than -0.5 V or higher than  $V_{CC} + 0.5$  V. During transitions, the voltage on any pin may undershoot to no less than -1.5 V or overshoot to no more than  $V_{CC} + 1.5$  V, for periods of less than 20 ns.

2. These parameters are tested initially and after a design or process change that affects the parameter according to appropriate AEC-Q100 and JEDEC test methods.

3. Page Mode,  $V_{CC}$  = 5 V, 25°C.

		V <sub>CC</sub> = 2.5	5 V – 5.5 V	
Symbol	Parameter	Min	Max	Units
f <sub>SCK</sub>	Clock Frequency	DC	10	MHz
t <sub>SU</sub>	Data Setup Time	10		ns
t <sub>H</sub>	Data Hold Time	10		ns
t <sub>WH</sub>	SCK High Time	40		ns
t <sub>WL</sub>	SCK Low Time	40		ns
t <sub>LZ</sub>	HOLD to Output Low Z		25	ns
t <sub>RI</sub> (Note 5)	Input Rise Time		2	μs
t <sub>FI</sub> (Note 5)	Input Fall Time		2	μs
t <sub>HD</sub>	HOLD Setup Time	0		ns
t <sub>CD</sub>	HOLD Hold Time	10		ns
t <sub>V</sub>	Output Valid from Clock Low		35	ns
t <sub>HO</sub>	Output Hold Time	0		ns
t <sub>DIS</sub>	Output Disable Time		20	ns
t <sub>HZ</sub>	HOLD to Output High Z		25	ns
t <sub>CS</sub>	CS High Time	40		ns
t <sub>CSS</sub>	CS Setup Time	30		ns
t <sub>CSH</sub>	CS Hold Time	30		ns
t <sub>CNS</sub>	CS Inactive Setup Time	20		ns
t <sub>CNH</sub>	CS Inactive Hold Time	20		ns
t <sub>WPS</sub>	WP Setup Time	10		ns
t <sub>WPH</sub>	WP Hold Time	10		ns
t <sub>WC</sub> (Note 6)	Write Cycle Time		5	ms

#### Table 5. A.C. CHARACTERISTICS ( $T_A = -40^{\circ}C$ to $+125^{\circ}C$ ) (Note 4)

4. AC Test Conditions:

4. AC lest Conditions: Input Pulse Voltages: 0.3 V<sub>CC</sub> to 0.7 V<sub>CC</sub> Input rise and fall times: ≤ 10 ns Input and output reference voltages: 0.5 V<sub>CC</sub> Output load: current source I<sub>OL max</sub>/I<sub>OH max</sub>; C<sub>L</sub> = 30 pF
5. This parameter is tested initially and after a design or process change that affects the parameter.

6. t<sub>WC</sub> is the time from the rising edge of CS after a valid write sequence to the end of the internal write cycle.

#### Table 6. POWER-UP TIMING (Notes 7, 8)

Symbol	Parameter		Мах	Units
t <sub>PUR</sub>	Power-up to Read Operation		1	ms
t <sub>PUW</sub>	Power-up to Write Operation	0.1	1	ms

7. This parameter is tested initially and after a design or process change that affects the parameter.

8. t<sub>PUR</sub> and t<sub>PUW</sub> are the delays required from the time V<sub>CC</sub> is stable at the operating voltage until the specified operation can be initiated.

#### **Pin Description**

SI: The serial data input pin accepts op-codes, addresses and data. In SPI modes (0,0) and (1,1) input data is latched on the rising edge of the SCK clock input.

**SO:** The serial data output pin is used to transfer data out of the device. In SPI modes (0,0) and (1,1) data is shifted out on the falling edge of the SCK clock.

**SCK:** The serial clock input pin accepts the clock provided by the host and used for synchronizing communication between host and CAV25010/20/40.

 $\overline{\text{CS}}$ : The chip select input pin is used to enable/disable the CAV25010/20/40. When  $\overline{\text{CS}}$  is high, the SO output is tri-stated (high impedance) and the device is in Standby Mode (unless an internal write operation is in progress). *Every communication session between host and CAV25010/20/40 must be preceded by a high to low transition and concluded with a low to high transition of the*  $\overline{\text{CS}}$  input.

 $\overline{WP}$ : The write protect input pin will allow all write operations to the device when held high. When  $\overline{WP}$  pin is tied low all write operations are inhibited.

**HOLD:** The HOLD input pin is used to pause transmission between host and CAV25010/20/40, without having to retransmit the entire sequence at a later time. To pause, HOLD must be taken low and to resume it must be taken back high, with the SCK input low during both transitions. When not used for pausing, the HOLD input should be tied to  $V_{CC}$ , either directly or through a resistor.

#### **Functional Description**

The CAV25010/20/40 devices support the Serial Peripheral Interface (SPI) bus protocol, modes (0,0) and (1,1). The device contains an 8-bit instruction register. The instruction set and associated op-codes are listed in Table 7.

Reading data stored in the CAV25010/20/40 is accomplished by simply providing the READ command and an address. Writing to the CAV25010/20/40, in addition to a WRITE command, address and data, also requires enabling the device for writing by first setting certain bits in a Status Register, as will be explained later.

After a high to low transition on the  $\overline{CS}$  input pin, the CAV25010/20/40 will accept any one of the six instruction op-codes listed in Table 7 and will ignore all other possible 8-bit combinations. The communication protocol follows the timing from Figure 2.

Instruction	Opcode	Operation			
WREN	0000 0110	Enable Write Operations			
WRDI	0000 0100	Disable Write Operations			
RDSR	0000 0101	Read Status Register			
WRSR	0000 0001	Write Status Register			
READ	0000 X011	Read Data from Memory			
WRITE	0000 X010	Write Data to Memory			

#### Table 7. INSTRUCTION SET (Note 9)

9. X = 0 for CAV25010, CAV25020. X = A8 for CAV25040

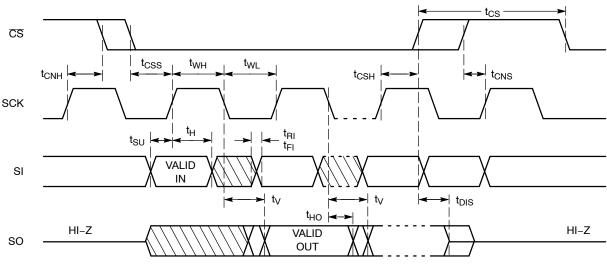


Figure 2. Synchronous Data Timing

#### **Status Register**

The Status Register, as shown in Table 8, contains a number of status and control bits.

The  $\overline{\text{RDY}}$  (Ready) bit indicates whether the device is busy with a write operation. This bit is automatically set to 1 during an internal write cycle, and reset to 0 when the device is ready to accept commands. For the host, this bit is read only.

The WEL (Write Enable Latch) bit is set/reset by the WREN/WRDI commands. When set to 1, the device is in a

Write Enable state and when set to 0, the device is in a Write Disable state.

The BP0 and BP1 (Block Protect) bits determine which blocks are currently write protected. They are set by the user with the WRSR command and are non-volatile. The user is allowed to protect a quarter, one half or the entire memory, by setting these bits according to Table 9. The protected blocks then become read-only.

#### Table 8. STATUS REGISTER

7	6	5	4	3	2	1	0
1	1	1	1	BP1	BP0	WEL	RDY

#### Table 9. BLOCK PROTECTION BITS

Status R	egister Bits		
BP1	BP0	Array Address Protected	Protection
0	0	None	No Protection
0	1	CAV25010: 060-07F, CAV25020: 0C0-0FF, CAV25040: 180-1FF	Quarter Array Protection
1	0	CAV25010: 040-07F, CAV25020: 080-0FF, CAV25040: 100-1FF	Half Array Protection
1	1	CAV25010: 000-07F, CAV25020: 000-0FF, CAV25040: 000-1FF	Full Array Protection

#### WRITE OPERATIONS

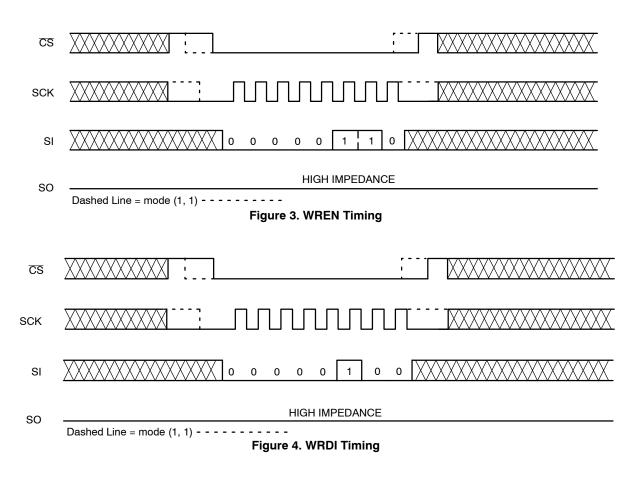
The CAV25010/20/40 device powers up into a write disable state. The device contains a Write Enable Latch (WEL) which must be set before attempting to write to the memory array or to the status register. In addition, the address of the memory location(s) to be written must be outside the protected area, as defined by BP0 and BP1 bits from the status register.

#### Write Enable and Write Disable

The internal Write Enable Latch and the corresponding Status Register WEL bit are set by sending the WREN

instruction to the CAV25010/20/40. Care must be taken to take the  $\overline{CS}$  input high after the WREN instruction, as otherwise the Write Enable Latch will not be properly set. WREN timing is illustrated in Figure 3. The WREN instruction must be sent prior to any WRITE or WRSR instruction.

The internal write enable latch is reset by sending the WRDI instruction as shown in Figure 4. Disabling write operations by resetting the WEL bit, will protect the device against inadvertent writes.



#### **Byte Write**

Once the WEL bit is set, the user may execute a write sequence, by sending a WRITE instruction, a 8-bit address and data as shown in Figure 5. For the CAV25040, bit 3 of the write instruction opcode contains A8 address bit. Internal programming will start after the low to high  $\overline{\text{CS}}$  transition. During an internal write cycle, all commands, except for RDSR (Read Status Register) will be ignored. The  $\overline{\text{RDY}}$  bit will indicate if the internal write cycle is in progress ( $\overline{\text{RDY}}$  high), or the device is ready to accept commands ( $\overline{\text{RDY}}$  low).

#### Page Write

After sending the first data byte to the CAV25010/20/40, the host may continue sending data, up to a total of 16 bytes, according to timing shown in Figure 6. After each data byte, the lower order address bits are automatically incremented, while the higher order address bits (page address) remain unchanged. If during this process the end of page is exceeded, then loading will "roll over" to the first byte in the page, thus possibly overwriting previously loaded data. Following completion of the write cycle, the CAV25010/20/40 is automatically returned to the write disable state.

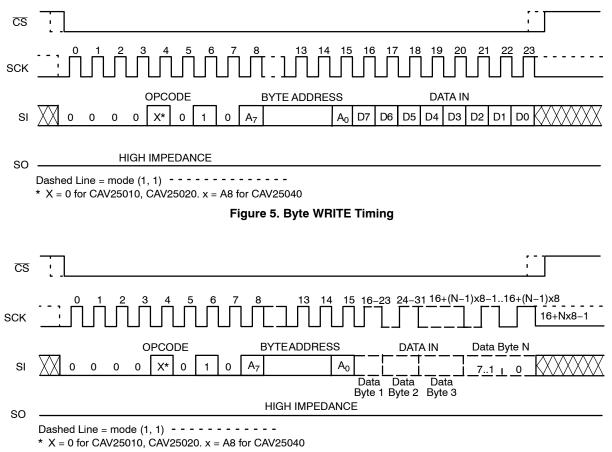


Figure 6. Page WRITE Timing

#### Write Status Register

The Status Register is written by sending a WRSR instruction according to timing shown in Figure 7. Only bits 2 and 3 can be written using the WRSR command.

#### Write Protection

When  $\overline{WP}$  input is low all write operations to the memory array and Status Register are inhibited.  $\overline{WP}$  going low while  $\overline{CS}$  is still low will interrupt a write operation. If the internal write cycle has already been initiated,  $\overline{WP}$  going low will have no effect on any write operation to the Status Register or memory array. The  $\overline{WP}$  input timing is shown in Figure 8.

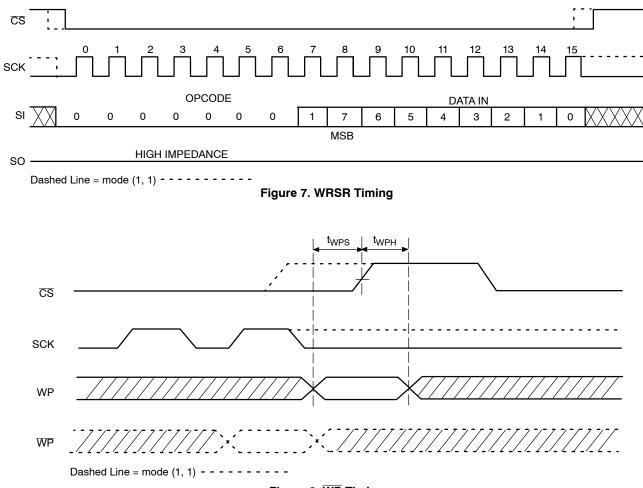


Figure 8. WP Timing

#### **READ OPERATIONS**

#### **Read from Memory Array**

To read from memory, the host sends a READ instruction followed by a 8-bit address (for the CAV25040, bit 3 of the read instruction opcode contains A8 address bit).

After receiving the last address bit, the CAV25010/20/40 will respond by shifting out data on the SO pin (as shown in Figure 9). Sequentially stored data can be read out by simply continuing to run the clock. The internal address pointer is automatically incremented to the next higher address as data is shifted out. After reaching the highest memory address, the address counter "rolls over" to the lowest memory address, and the read cycle can be continued indefinitely. The read operation is terminated by taking  $\overline{CS}$  high.

#### **Read Status Register**

To read the status register, the host simply sends a RDSR command. After receiving the last bit of the command, the CAV25010/20/40 will shift out the contents of the status register on the SO pin (Figure 10). The status register may be read at any time, including during an internal write cycle.

While the internal write cycle is in progress, the RDSR command will output the full content of the status register. For easy detection of the internal write cycle completion, both during writing to the memory array and to the status register, we recommend sampling the RDY bit only through the polling routine. After detecting the RDY bit "0", the next RDSR instruction will always output the expected content of the status register.

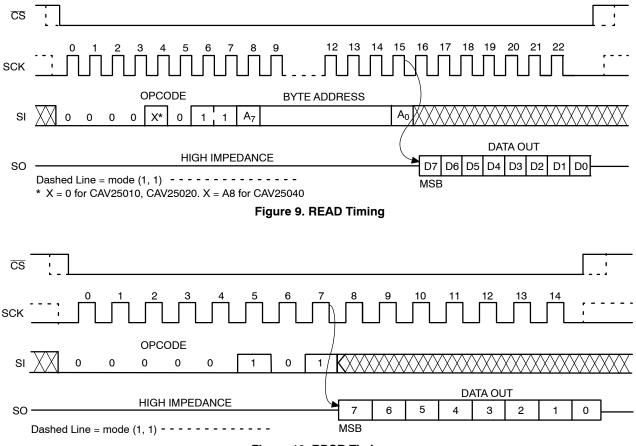


Figure 10. RDSR Timing

#### **Hold Operation**

The  $\overline{\text{HOLD}}$  input can be used to pause communication between host and CAV25010/20/40. To pause,  $\overline{\text{HOLD}}$  must be taken low while SCK is low (Figure 11). During the hold condition the device must remain selected ( $\overline{\text{CS}}$  low). During the pause, the data output pin (SO) is tri-stated (high impedance) and SI transitions are ignored. To resume communication,  $\overline{\text{HOLD}}$  must be taken high while SCK is low.

#### **Design Considerations**

The CAV25010/20/40 devices incorporate Power–On Reset (POR) circuitry which protects the internal logic against powering up in the wrong state. The device will power up into Standby mode after  $V_{CC}$  exceeds the POR trigger level and will power down into Reset mode when

 $V_{CC}$  drops below the POR trigger level. This bi-directional POR behavior protects the device against 'brown-out' failure following a temporary loss of power.

The CAV25010/20/40 device powers up in a write disable state and in a low power standby mode. A WREN instruction must be issued prior to any writes to the device.

After power up, the  $\overline{CS}$  pin must be brought low to enter a ready state and receive an instruction. After a successful byte/page write or status register write, the device goes into a write disable mode. The  $\overline{CS}$  input must be set high after the proper number of clock cycles to start the internal write cycle. Access to the memory array during an internal write cycle is ignored and programming is continued. Any invalid op-code will be ignored and the serial output pin (SO) will remain in the high impedance state.

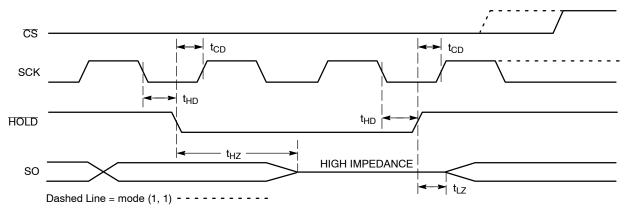
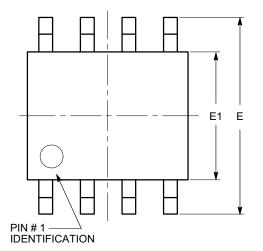


Figure 11. HOLD Timing

## **Onsem**í.

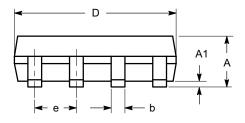
SOIC-8, 150 mils CASE 751BD ISSUE O

DATE 19 DEC 2008



TOP VIEW

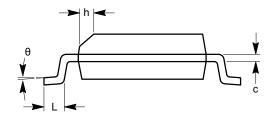
SYMBOL	MIN	NOM	MAX
А	1.35		1.75
A1	0.10		0.25
b	0.33		0.51
с	0.19		0.25
D	4.80		5.00
E	5.80		6.20
E1	3.80		4.00
е		1.27 BSC	
h	0.25		0.50
L	0.40		1.27
θ	0°		8°



SIDE VIEW

#### Notes:

(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MS-012.

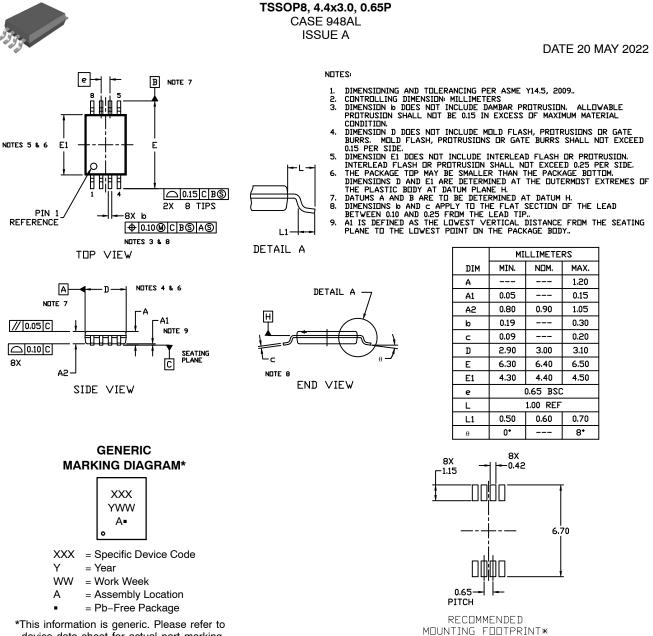


END VIEW

DOCUMENT NUMBER:	98AON34272E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC 8, 150 MILS PAGE 1 OF				
the right to make changes without furth purpose, nor does <b>onsemi</b> assume an	er notice to any products herein. <b>onsemi</b> make ny liability arising out of the application or use	LLC dba <b>onsemi</b> or its subsidiaries in the United States and/or other cour es no warranty, representation or guarantee regarding the suitability of its pr of any product or circuit, and specifically disclaims any and all liability, incl e under its patent rights nor the rights of others.	oducts for any particular		

#### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

# onsemi



device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may \* or may not be present. Some products may not follow the Generic Marking.

\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DOCUMENT NUMBER:	98AON34428E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP8, 4.4X3.0, 0.65P		PAGE 1 OF 1
onsemi and ONSEMI: are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.			

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

#### TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative